

N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR

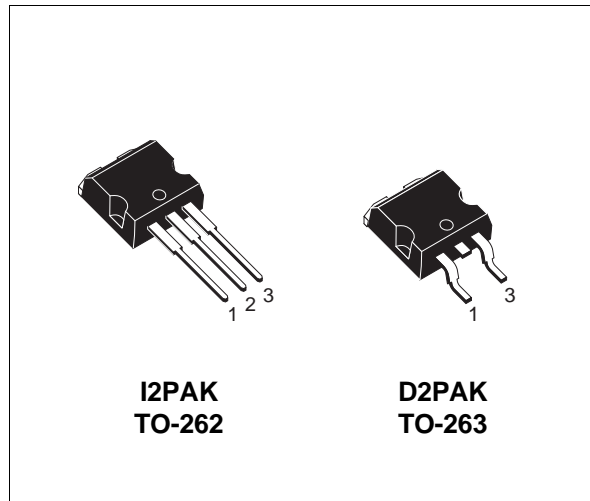
PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STB45N10L	100 V	< 0.036 Ω	45 A

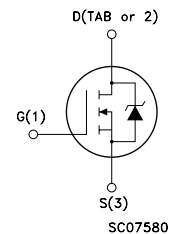
- TYPICAL R_{DS(on)} = 0.028 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW INPUT CAPACITANCE
- LOW GATE CHARGE
- LOW LEAKAGE CURRENT
- APPLICATION ORIENTED CHARACTERIZATION
- THROUGH-HOLE I2PAK (TO-262) POWER PACKAGE IN TUBE (SUFFIX "-1")
- SURFACE-MOUNTING D2PACK (TO-263) POWER PACKAGE IN TUBE (NO SUFFIX) OR IN TAPE & REEL (SUFFIX "T4")

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLY (SMPS)
- CONSUMER AND INDUSTRIAL LIGHTING
- DC-AC CONVERTER FOR WELDING EQUIPMENT AND UNINTERRUPTABLE POWER SUPPLY (UPS)



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	100	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	100	V
V _{GS}	Gate-source Voltage	± 15	V
I _D	Drain Current (continuous) at T _c = 25 °C	45	A
I _D	Drain Current (continuous) at T _c = 100 °C	32	A
I _{DM} (•)	Drain Current (pulsed)	180	A
P _{tot}	Total Dissipation at T _c = 25 °C	150	W
	Derating Factor	1	W/°C
T _{stg}	Storage Temperature	-65 to 175	°C
T _j	Max. Operating Junction Temperature	175	°C

(•) Pulse width limited by safe operating area

STB45N10L

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W
R _{thj-amb}	Thermal Resistance Case-sink	Typ	0.5	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max, δ < 1%)	45	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 25 V)	400	mJ
E _{AR}	Repetitive Avalanche Energy (pulse width limited by T _j max, δ < 1%)	100	mJ
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (T _c = 100 °C, pulse width limited by T _j max, δ < 1%)	32	A

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA V _{GS} = 0	100			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating x 0.8 T _c = 125 °C			250 1000	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 15 V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	1	1.7	2.5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 5 V I _D = 22.5 A V _{GS} = 5 V I _D = 22.5 A T _c = 100 °C V _{GS} = 10 V I _D = 22.5 A V _{GS} = 10 V I _D = 22.5 A T _c = 100 °C		0.028 0.024	0.036 0.032 0.064	Ω Ω Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} x R _{DS(on)max} V _{GS} = 10 V	45			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} x R _{DS(on)max} I _D = 22.5 A	20	43		S
C _{iss}	Input Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		3700	4700	pF
C _{oss}	Output Capacitance			600	800	pF
C _{rss}	Reverse Transfer Capacitance			170	230	pF

ELECTRICAL CHARACTERISTICS (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	$V_{DD} = 50\text{ V}$ $R_G = 4.7\ \Omega$		25 100	35 140	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 80\text{ V}$ $R_G = 47\ \Omega$		130		A/ μ s
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 80\text{ V}$ $I_D = 45\text{ A}$ $V_{GS} = 5\text{ V}$		70 15 35	100	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 80\text{ V}$ $R_G = 4.7\ \Omega$		40 90 130	60 130 190	ns ns ns

SOURCE DRAIN DIODE

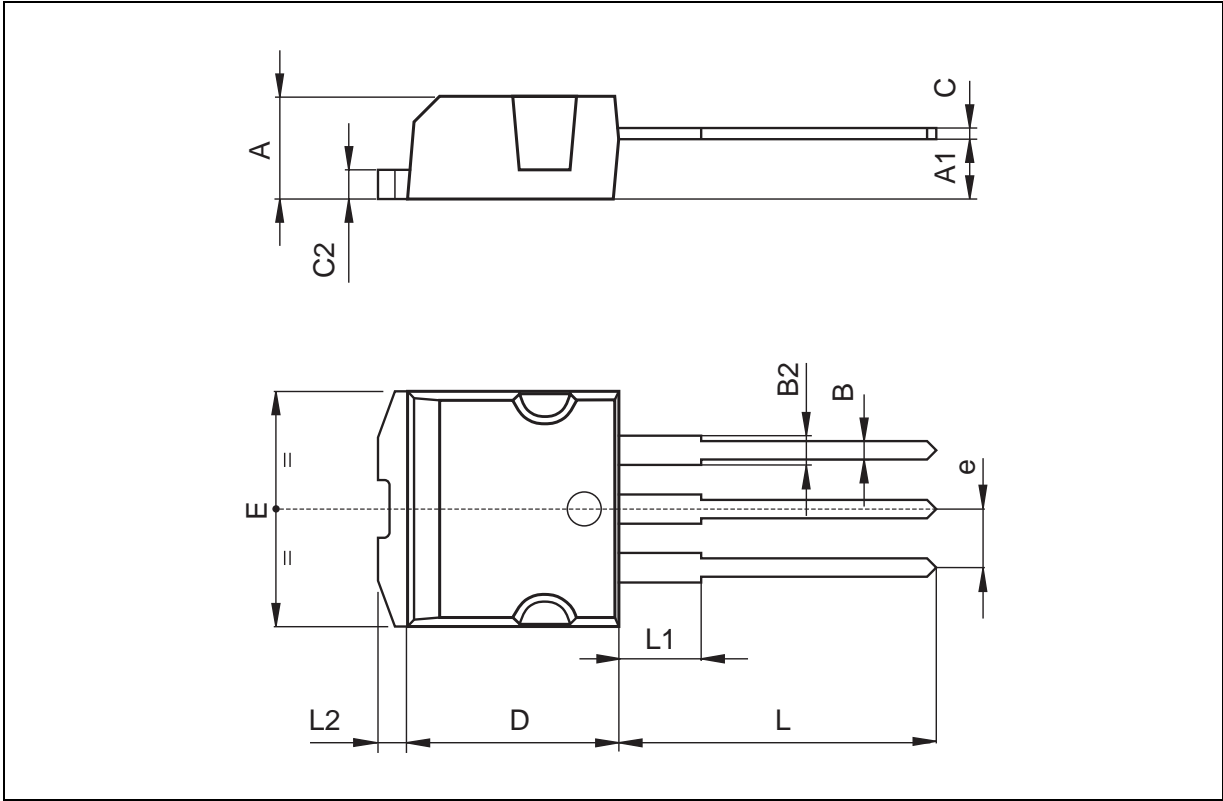
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}(\bullet)$	Source-drain Current Source-drain Current (pulsed)				45 180	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 45\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 45\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 30\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		165 0.1 12		ns μ C A

(*) Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

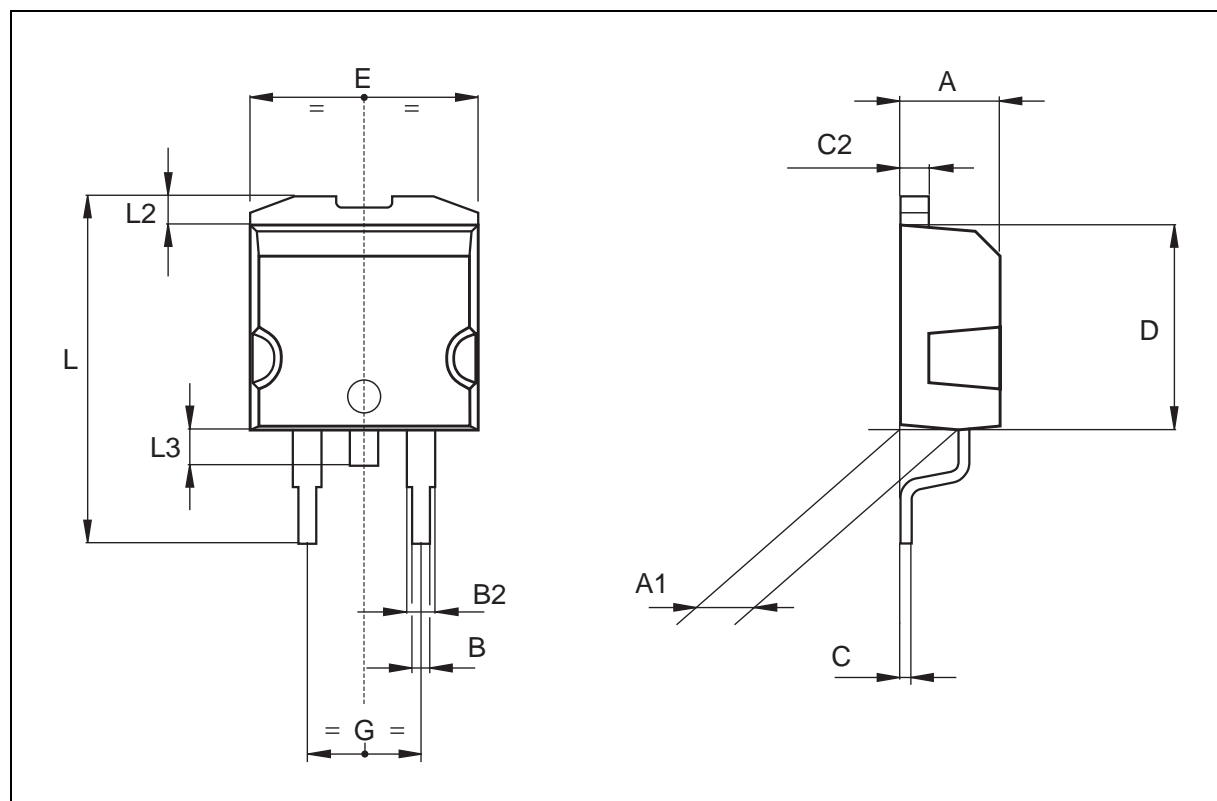
TO-262 (I2PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.3		4.6	0.169		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B1	1.2		1.38	0.047		0.054
B2	1.25		1.4	0.049		0.055
C	0.45		0.6	0.017		0.023
C2	1.21		1.36	0.047		0.053
D	9		9.35	0.354		0.368
e	2.44		2.64	0.096		0.104
E	10		10.28	0.393		0.404
L	13.2		13.5	0.519		0.531
L1	3.48		3.78	0.137		0.149
L2	1.27		1.37	0.050		0.054



TO-263 (D2PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.3		4.6	0.169		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.25		1.4	0.049		0.055
C	0.45		0.6	0.017		0.023
C2	1.21		1.36	0.047		0.053
D	9		9.35	0.354		0.368
E	10		10.28	0.393		0.404
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.624
L2	1.27		1.37	0.050		0.054
L3	1.4		1.75	0.055		0.068



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